by IMFEDK2010 Committee, IEEE EDS Kansai Chapter

Second Call for Papers

IMFEDK 2010 Awards

■ IEEE EDS Kansai Chapter IMFEDK Best Paper Award

Paper ID: C-3

Titled: “*Demonstration of High Channel Mobility in 4H-SiC MOSFETs by Utilizing Phosphorus-Doped Gate Oxide*”

Authors: **Dai Okamoto**, H. Yano, K. Hirata, S. Kotake, T. Hatayama, T. Fuyuki

Affiliation: Nara Institute of Science and Technology

■ IEEE EDS Kansai Chapter IMFEDK Student Paper Award

Author: **Yosuke Tojo**[1], Paper ID: PA-4

Titled: *“Location Controls of Crystallized Areas in Silicon Films Utilizing Cage Shape Protein”*

Coauthors: A. Miura[1,2], I. Yamashita[1,3,4], Y. Uraoka[1,4] ,

Affiliation: [1]Nara Institute of Science and Technology, [2]National Chiao Tung University, [3]Panasonic, [4]CREST

Author: **Hideo Shimizu**, Paper ID: PA-12

Titled: *“Reduction of self-heating effect in silicon MOSFETs on directly bonded Si-on-SiC wafer with high heat conductance ”*

Coauthor: R. Araki, H. Shinohara, H. Kinoshita, M. Yoshimoto

Affiliation: Kyoto Institute of Technology

Author: **Daishi Ino**, Paper ID: PA-16

Titled: *“Performance Evaluation of 1-V Deep Sub-micron Dynamic-Threshold SOI MOSFET”*

Coauthors: T. Tochio, Y. Omura

Affiliation: Kansai University

Author: **Yuta Goto**, Paper ID: PB-4

Titled: *“Chemical Bonding Features at TiO2/Pt Interface and Their Impact on Resistance-Switching Properties”*

Coauthors: A. Ohta, H. Murakami, S. Higashi, S. Miyazaki

Affiliation: Hiroshima University

Author: **Kumiho Tsuji**, Paper ID: PC-4

Titled: *“Micro-fabrication and characterization of an ion-sensitive ZnO-based transistor on a glass substrate”*

Coauthors: K. Koike, K. Ogata, S. Sasa, M. Inoue, M. Yano

Affiliation: Osaka Institute of Technology